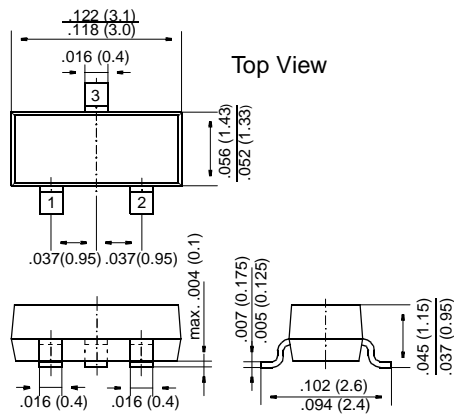


# BS829

## DMOS Transistors (P-Channel)

### SOT-23



Dimensions in inches and (millimeters)

Pin configuration

1 = Gate, 2 = Source, 3 = Drain

### FEATURES

- ◆ High input impedance
- ◆ Low gate threshold voltage
- ◆ Low drain-source ON resistance
- ◆ High-speed switching
- ◆ No minority carrier storage time
- ◆ CMOS logic compatible input
- ◆ No thermal runaway
- ◆ No secondary breakdown



### MECHANICAL DATA

**Case:** SOT-23 Plastic Package

**Weight:** approx. 0.008 g

**Marking**

S29

## MAXIMUM RATINGS AND ELECTRICAL CHARACTERISTICS

Ratings at 25 °C ambient temperature unless otherwise specified

	Symbol	Value	Unit
Drain-Source Voltage	$-V_{DSS}$	400	V
Drain-Gate Voltage	$-V_{DGS}$	400	V
Gate-Source Voltage (pulsed)	$V_{GS}$	$\pm 20$	V
Drain Current (continuous) at $T_{SB} = 50^\circ\text{C}$	$-I_D$	70	mA
Power Dissipation at $T_{SB} = 50^\circ\text{C}$	$P_{tot}$	350 <sup>1)</sup>	mW
Junction Temperature	$T_j$	150	°C
Storage Temperature Range	$T_S$	-65 to +150	°C

<sup>1)</sup> Device on fiberglass substrate, see layout

### Inverse Diode

	Symbol	Value	Unit
Max. Forward Current (continuous) at $T_{amb} = 25^\circ\text{C}$	$I_F$	350	mA
Forward Voltage Drop (typ.) at $V_{GS} = 0\text{ V}$ , $I_F = 350\text{ mA}$ , $T_j = 25^\circ\text{C}$	$V_F$	1.0	V

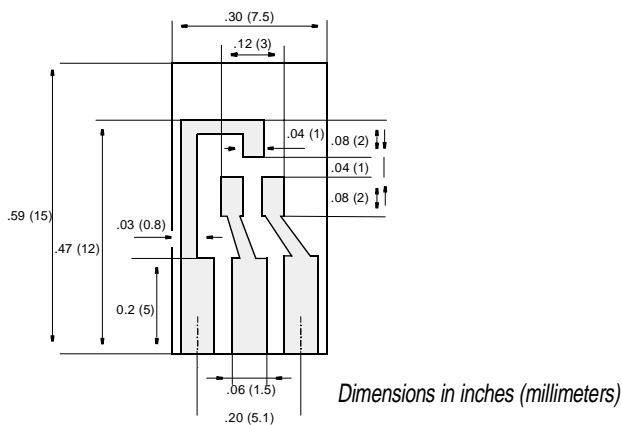
# BS829

## ELECTRICAL CHARACTERISTICS

Ratings at 25 °C ambient temperature unless otherwise specified

	Symbol	Min.	Typ.	Max.	Unit
Drain-Source Breakdown Voltage at $-I_D = 100 \mu\text{A}$ , $V_{GS} = 0 \text{ V}$	$-V_{(BR)DSS}$	400	430	–	V
Gate-Body Leakage Current, Forward at $-V_{GSF} = 20 \text{ V}$ , $V_{DS} = 0 \text{ V}$	$-I_{GSSF}$	–	–	100	nA
Gate-Body Leakage Current, Reverse at $-V_{GSR} = 20 \text{ V}$ , $V_{DS} = 0 \text{ V}$	$-I_{GSSR}$	–	–	100	nA
Drain Cutoff Current at $-V_{DS} = 400 \text{ V}$ , $V_{GS} = 0 \text{ V}$	$-I_{DSS}$	–	–	500	$\mu\text{A}$
Gate-Source Threshold Voltage at $V_{GS} = V_{DS}$ , $-I_D = 250 \mu\text{A}$	$-V_{GS(th)}$	1	1.5	2.5	V
Drain-Source ON Resistance at $V_{GS} = 5 \text{ V}$ , $-I_D = 100 \text{ mA}$	$R_{DS(on)}$	–	40	50	$\Omega$
Capacitance at $-V_{DS} = 25 \text{ V}$ , $V_{GS} = 0 \text{ V}$ , $f = 1 \text{ MHz}$					
Input Capacitance	$C_{iSS}$	–	200	–	pF
Output Capacitance	$C_{oSS}$	–	30	–	pF
Feedback Capacitance	$C_{rSS}$	–	10	–	pF
Switching Times at $-V_{GS} = 10 \text{ V}$ , $-V_{DS} = 10 \text{ V}$ , $R_D = 100 \Omega$					
Turn-On Time	$t_{on}$	–	10	–	ns
Turn-Off Time	$t_{off}$	–	50	–	ns
Thermal Resistance Junction to Ambient Air	$R_{thJA}$	–	–	320 <sup>1)</sup>	K/W

1) Device on fiberglass substrate, see layout



### Layout for $R_{thJA}$ test

Thickness: Fiberglass 0.059 in (1.5 mm)  
Copper leads 0.012 in (0.3 mm)